

Silicon PNP Power Transistors

2SB794 2SB795

DESCRIPTION

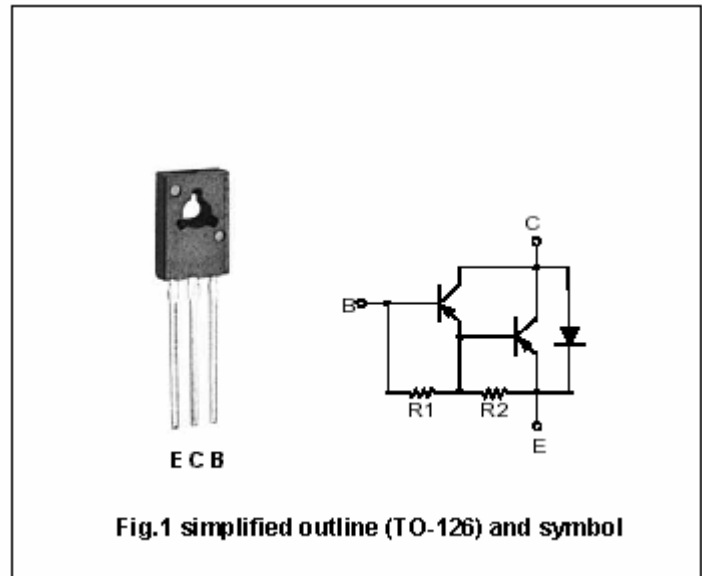
- With TO-126 package
- DARLINGTON
- High DC current gain
- Low collector saturation voltage
- Complement to type 2SD985 2SD986

APPLICATIONS

- For use in operating from IC without predriver ,such as hammer driver

PINNING(See Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SB794	-60	V
		2SB795	-80	
V _{CEO}	Collector-emitter voltage	2SB794	-60	V
		2SB795	-80	
V _{EBO}	Emitter-base voltage	Open collector	-8	V
I _C	Collector current (DC)		-1.5	A
I _{CM}	Collector current-peak		-3.0	A
P _D	Total power dissipation	T _a =25□	1.0	W
		T _C =25□	10	
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SB794	$I_C=-10mA ; I_B=0$	-60			V
		2SB795		-80			
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-1A ; I_B=-1mA$			-1.5	V	
V_{BEsat}	Base-emitter saturation voltage	$I_C=-1A ; I_B=-1mA$			-2.0	V	
I_{CBO}	Collector cut-off current	2SB794	$V_{CB}=-60V ; I_E=0$			-1.0	μA
		2SB795		$V_{CB}=-80V ; I_E=0$			
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V ; I_C=0$			-2.0	mA	
h_{FE-1}	DC current gain	$I_C=-0.5A ; V_{CE}=-2V$	1000				
h_{FE-2}	DC current gain	$I_C=-1A ; V_{CE}=-2V$	2000		30000		

Switching times

t_{on}	Turn-on time	$I_C=-1.0A ; I_{B1}=-I_{B2}=-1.0mA$ $V_{CC}=-50V ; R_L=50\Omega$		0.5		μs
t_{stg}	Storage time			1.0		μs
t_f	Fall time			1.0		μs

◆ h_{FE-2} Classifications

M	L	K
2000-5000	4000-10000	8000-30000

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PACKAGE OUTLINE

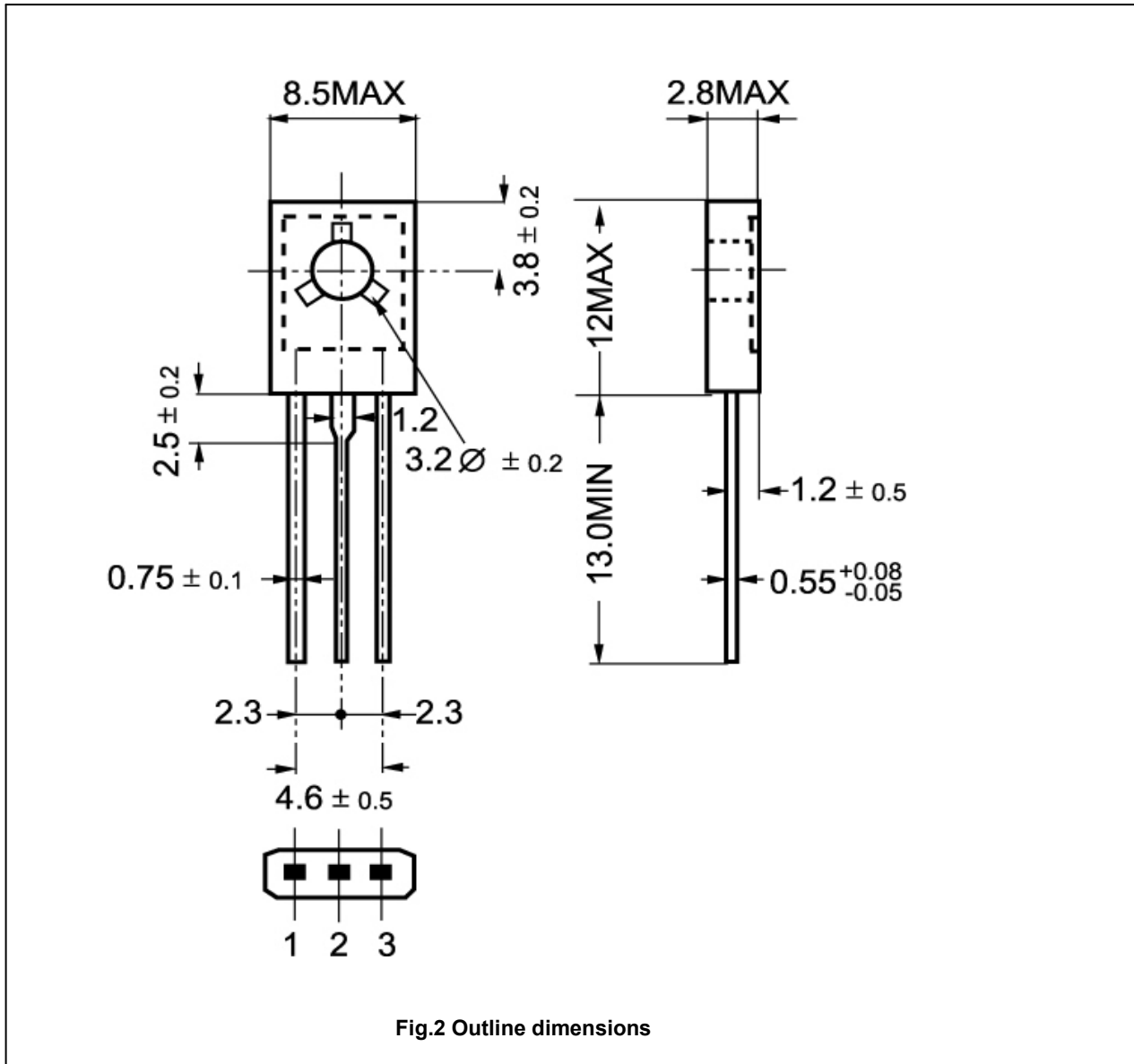


Fig.2 Outline dimensions